



I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

PATENT
Attorney Docket No.: 000939-073311US
Client Ref. No.: P01HA010/US

On July 25, 2003

TOWNSEND and TOWNSEND and CREW LLP

By: [Signature]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hong Koo Kim

Application No.: 09/747,779

Filed: December 22, 2000

For: FABRICATION METHOD AND
STRUCTURE FOR FERROELECTRIC
NONVOLATILE MEMORY FIELD
EFFECT TRANSISTOR

Examiner: Marcos D. Pizarro Crespo

Technology Center/Art Unit: 2814

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 6 of this paper.

07/29/2003 HBERHE 00000135 201430 09747779
01 FC:1202 126.00 DA
02 FC:1201 84.00 DA